

N-Channel Enhancement Mode MOSFET

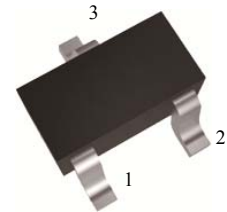
Feature

- 30V/5.8A, $R_{DS(ON)} = 35m\Omega(MAX) @V_{GS} = 10V$.
 $R_{DS(ON)} = 40m\Omega(MAX) @V_{GS} = 4.5V$.
 $R_{DS(ON)} = 55m\Omega(MAX) @V_{GS} = 2.5V$.
- Super High dense cell design for extremely low $R_{DS(ON)}$.
- Reliable and Rugged.
- SC-59 for Surface Mount Package.

Applications

- Power Management
- Portable Equipment and Battery Powered Systems.

SC-59



1 : Gate 2 : Source 3 : Drain

Absolute Maximum Ratings TA=25°C Unless Otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous	I_D	5.8	A

Electrical Characteristics TA=25°C Unless Otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ.	Max	Units
Off Characteristics						
Drain to Source Breakdown Voltage	BVDSS	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$	-	-	1	μA
Gate Body Leakage Current, Forward	I_{GSSF}	$V_{GS}=12V, V_{DS}=0V$	-	-	100	nA
Gate Body Leakage Current, Reverse	I_{GSSR}	$V_{GS}=-12V, V_{DS}=0V$	-	-	-100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	0.6	-	1.5	V
Static Drain-source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=5.8A$	-	30	35	$m\Omega$
		$V_{GS}=4.5V, I_D=5A$	-	33	40	$m\Omega$
		$V_{GS}=2.5V, I_D=4A$	-	45	55	$m\Omega$
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Voltage	VSD	$V_{GS}=0V, I_S=1.25A$			1.2	V

Dynamic

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
Q_g	Total Gate Charge	$V_{DS}=15V, V_{GS}=10V, I_D=2A$		8.5	12	nC
Q_{gs}	Gate-Source Charge			1.1		
Q_{gd}	Gate-Drain Charge			1.8		
t_{on}	Turn-on Time	$V_{DD}=15V, I_D=2A, V_{GS}=10V, R_G=6\Omega$			40	ns
$t_{d(ON)}$	Turn-on Delay time			11		
t_r	Turn-on Rise Time			17		
$T_{d(off)}$	Turn-off Delay Time			37		
t_f	Turn-off Fall Time			20		
t_{off}	Turn-off Time				60	

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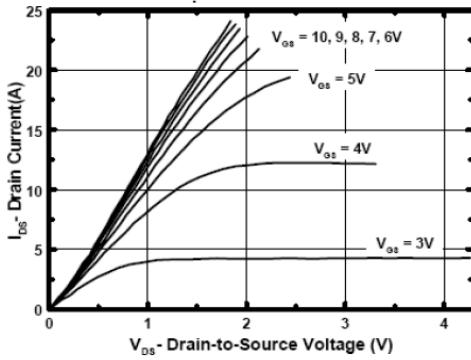


Figure 1. Output Characteristics

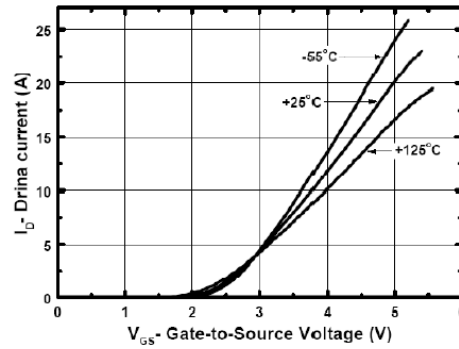


Figure 2. Transfer Characteristics

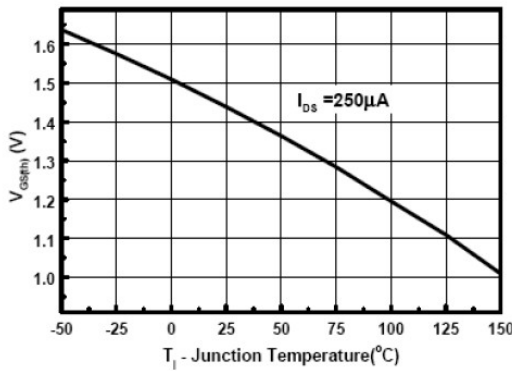


Figure 3. Gate Threshold Variation with Temperature

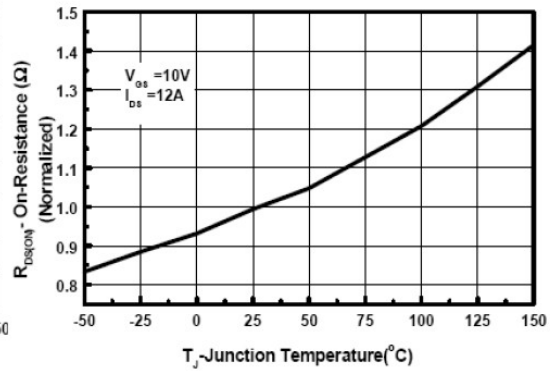


Figure 4. On-Resistance Variation with Temperature

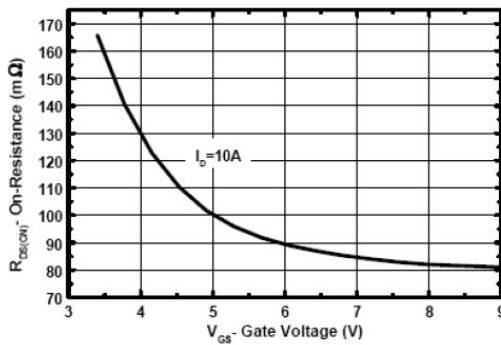


Figure 5. On-Resistance vs. Gate-to-Source Voltage

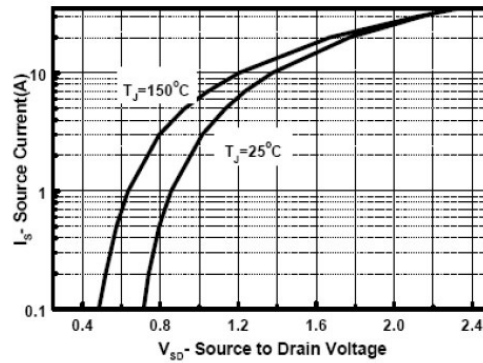
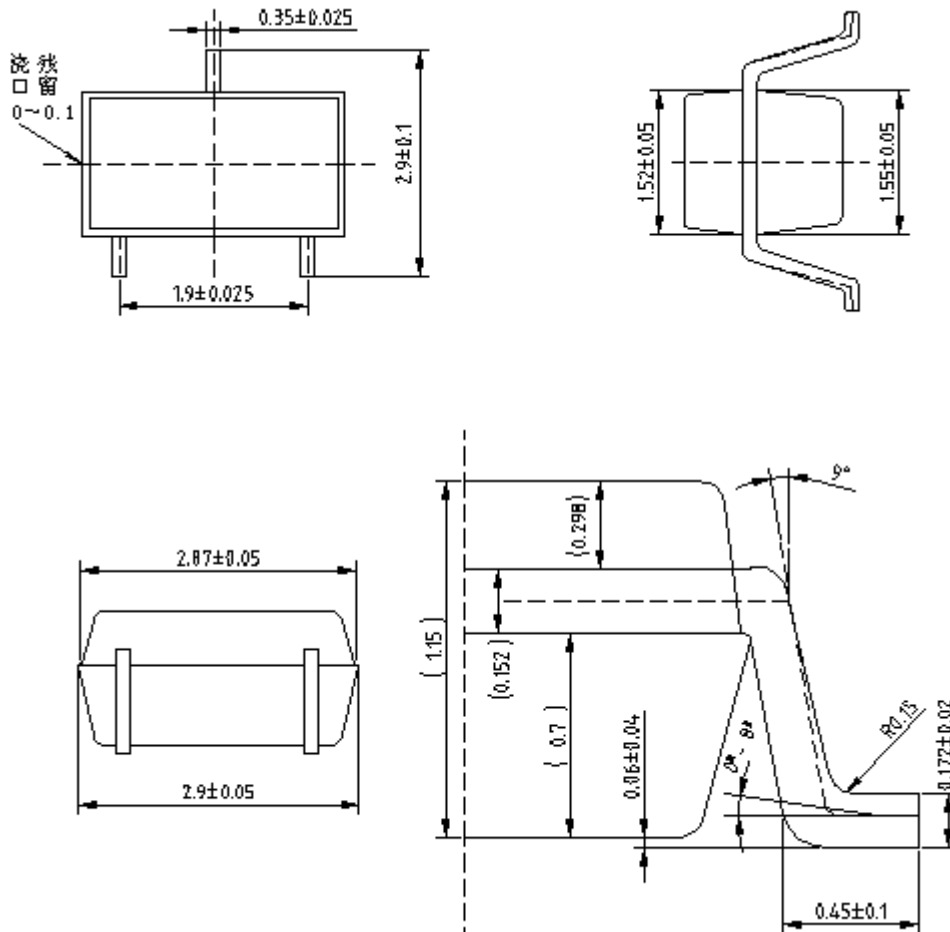


Figure 6. Source-Drain Diode Forward Voltage



Package Outline Dimensions (UNIT: mm)

SC-59



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